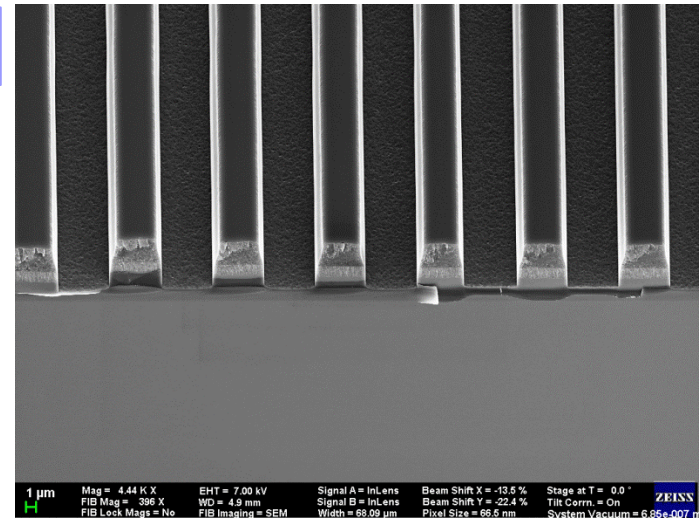


PECVD Silicon Oxide and Nitride Trenches

Etching Mask: 3.5 μm photoresist S1822

Process Condition

Parameter	Value
C4F8 (sccm)	10
SF6 (sccm)	10
Pressure (mTorr)	3
Coil Power (W)	800
Platen Power (W)	100
Temperature ($^{\circ}\text{C}$) (lid/wall/chuck)	40/40/21



Result

Parameter	Value
Etch Rate ($\mu\text{m}/\text{min}$)	0.4
Etch Profile	89 $^{\circ}$
Selectivity to Al	~1.5:1